

1-Line Bi-directional ESD Protection Diode

Description

These surge protection diodes are designed for applications requiring transient over voltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. These devices are ideal for situations where board space is at a premium.

Features

Bi-directional ESD protection of one line

• Reverse stand-off voltage: 5.0V Max

Low leakage current: nA Level

Response time is typically < 1 ns

Complies with following standards:

—IEC 61000-4-2 (ESD) immunity test

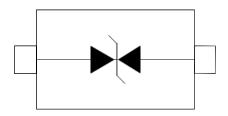
Air discharge: ±30kV

Contact discharge: ±30kV

—IEC61000-4-5 (Lightning) 25A (8/20μs)

RoHS Compliant

Schematic and Pin Configuration



SOD-323 (Top View)

Circuit Schematic

Mechanical Characteristics

- SOD-323 Small Outline Plastic Package
- Level 1 moisture sensitivity per J-STD-020
- Case Material: "Green" Molding Compound
- Lead Finish: Matte Tin
- We declare that the material of product compliance with RoHS requirements and Halogen Free

Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA'S)
- Wireless Systems
- Notebooks, Desktops, and Servers

Marking Information



5/9 = Device Marking Code

Ordering Information

| Part Number | Shipping | Reel Size |
|-------------|-----------------|--------------|
| PSD05C | 3000/Tape &Reel | 7 inch |



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

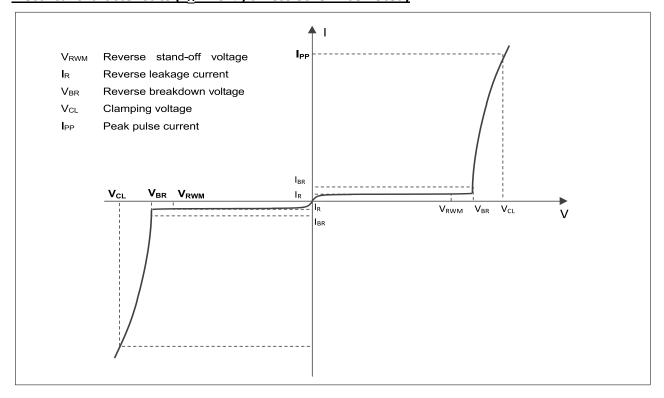
| Parameter | Symbol | Value | Unit |
|---------------------------------|------------------|--------------------|------|
| Peak Pulse Power (8/20μs) | РРК | 500 | W |
| Peak Pulse Current (8/20µs) | I _{PP} | 25 | A |
| ESD per IEC 61000-4-2 (Air) | V | ±30 | kV |
| ESD per IEC 61000-4-2 (Contact) | VESD | ±30 | kV |
| Lead temperature | T∟ | 260 | °C |
| Operating Temperature Range | T _{OP} | -40 ~ +85 | °C |
| Storage Temperature Range | T _{STG} | −55 ~ + 150 | °C |

Electrical Characteristics (TA=25°C unless otherwise specified)

| Parameter | Symbol | Min | Тур | Max | Unit | Test Condition |
|---------------------------|------------------|-----|-----|-----|------|--------------------------------------|
| Reverse Working Voltage | V _{RWM} | | | 5.0 | V | |
| Reverse Breakdown Voltage | V_{BR} | 5.5 | | 8.5 | V | $I_T = 1 \text{mA}$ |
| Reverse Leakage Current | I _R | | | 200 | nA | V _{RWM} =5.0 V |
| Clamping Voltage | Vc | | | 8.5 | V | I _{PP} = 10A (8/20µs pulse) |
| Clamping Voltage | Vc | | | 20 | V | I _{PP} = 25A (8/20µs pulse) |
| Junction Capacitance | Сл | | 60 | 80 | pF | V _R = 0V, f = 1MHz |



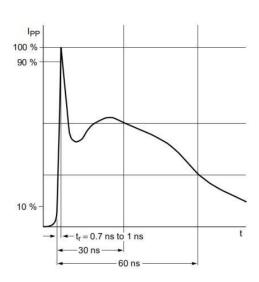
Electrical characteristics (T_A = 25 °C, unless otherwise noted)



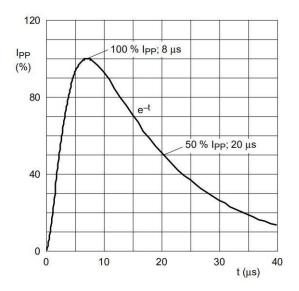
Definitions of electrical characteristics



Typical Performance Characteristics (TA=25°C unless otherwise Specified



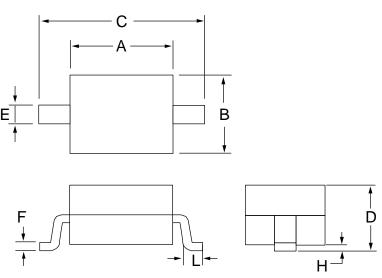
IEC61000-4-2 Waveform



IEC 61000-4-5 Waveform(8/20µs pulse)

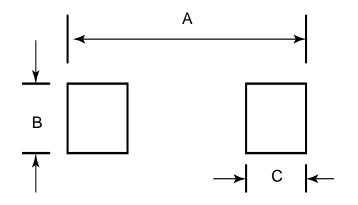


SOD-323 Package Outline Drawing



| SYM | DIMENSIONS | | | | | |
|-----|-------------|------|------|-------|-------|--|
| | MILLIMETERS | | | INC | HES | |
| | MIN | NOM | MAX | MIN | MAX | |
| Α | 1.50 | 1.65 | 1.80 | 0.060 | 0.071 | |
| В | 1.20 | 1.30 | 1.40 | 0.045 | 0.054 | |
| С | 2.30 | 2.50 | 2.70 | 0.090 | 0.107 | |
| D | - | | 1.10 | - | 0.043 | |
| Е | 0.30 | | 0.40 | 0.012 | 0.016 | |
| F | 0.10 | | 0.25 | 0.004 | 0.010 | |
| L | 0.20 | | 0.40 | 0.008 | 0.016 | |
| Н | - | | 0.10 | - | 0.004 | |

Suggested Land Pattern

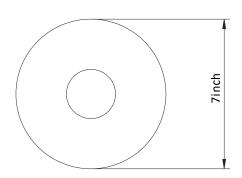


| SYM | DIMENSIONS | | | | |
|-------|-------------|--------|--|--|--|
| 01111 | MILLIMETERS | INCHES | | | |
| А | 3.15 | 0.120 | | | |
| В | 0.80 | 0.031 | | | |
| С | 0.80 | 0.031 | | | |

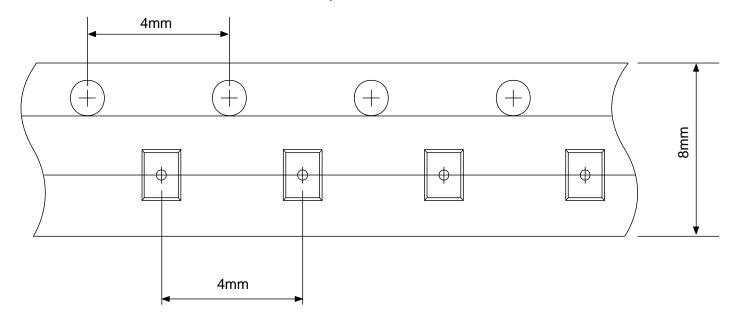


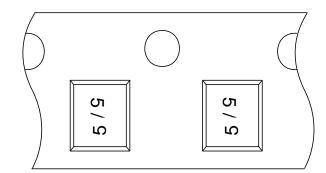
TAPE AND REEL INFORMATION

Reel Dimensions



Tape Dimensions









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